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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	e200z4d
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	147
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 27x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc564b64l7c8e0x

Revision history 118

1 Introduction

1.1 Document Overview

This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the SPC564Bxx and SPC56ECxx device. To ensure a complete understanding of the device functionality, refer also to the SPC564Bxx and SPC56ECxx Reference Manual.

1.2 Description

The SPC564Bxx and SPC56ECxx is a new family of next generation microcontrollers built on the Power Architecture embedded category. This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the device.

The SPC564Bxx and SPC56ECxx family expands the range of the SPC560B microcontroller family. It provides the scalability needed to implement platform approaches and delivers the performance required by increasingly sophisticated software architectures. The advanced and cost-efficient host processor core of the SPC564Bxx and SPC56ECxx automotive controller family complies with the Power Architecture embedded category, which is 100 percent user-mode compatible with the original Power Architecture user instruction set architecture (UISA). It operates at speeds of up to 120 MHz and offers high performance processing optimized for low power consumption. It also capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

2.3 Functional ports

The functional port pins are listed in *Table 5*.

Table 5. Functional port pin descriptions

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PA[0]	PCR[0]	AF0 AF1 AF2 AF3 — —	GPIO[0] E0UC[0] CLKOUT E0UC[13] WKPU[19] CAN1RX	SIUL eMIOS_0 MC_CGM eMIOS_0 WKPU FlexCAN_1	I/O I/O O I/O I I	M/S	Tristate	24	24	G4
PA[1]	PCR[1]	AF0 AF1 AF2 AF3 — — —	GPIO[1] E0UC[1] — — WKPU[2] CAN3RX NMI[0][3]	SIUL eMIOS_0 — — WKPU FlexCAN_3 WKPU	I/O I/O — — I I I	S	Tristate	19	19	F3
PA[2]	PCR[2]	AF0 AF1 AF2 AF3 — —	GPIO[2] E0UC[2] — MA[2] WKPU[3] NMI[1][3]	SIUL eMIOS_0 — ADC_0 WKPU WKPU	I/O I/O — O I I	S	Tristate	17	17	F1
PA[3]	PCR[3]	AF0 AF1 AF2 AF3 — — —	GPIO[3] E0UC[3] LIN5TX CS4_1 RX_ER_CLK EIRQ[0] ADC1_S[0]	SIUL eMIOS_0 LINFlexD_5 DSPI_1 FEC SIUL ADC_1	I/O I/O O O I I I	M/S	Tristate	114	138	G16
PA[4]	PCR[4]	AF0 AF1 AF2 AF3 — —	GPIO[4] E0UC[4] — CS0_1 LIN5RX WKPU[9]	SIUL eMIOS_0 — DSPI_1 LINFlexD_5 WKPU	I/O I/O — I/O I I	S	Tristate	51	61	T2

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PF[8]	PCR[88]	AF0 AF1 AF2 AF3	GPIO[88] CAN3TX CS4_0 CAN2TX	SIUL FlexCAN_3 DSPI_0 FlexCAN_2	I/O O O O	M/S	Tristate	42	50	N2
PF[9]	PCR[89]	AF0 AF1 AF2 AF3 — — —	GPIO[89] E1UC[1] CS5_0 — CAN2RX CAN3RX WKPU[22]	SIUL eMIOS_1 DSPI_0 — FlexCAN_2 FlexCAN_3 WKPU	I/O I/O O — I I I	S	Tristate	41	49	M4
PF[10]	PCR[90]	AF0 AF1 AF2 AF3	GPIO[90] CS1_0 LIN4TX E1UC[2]	SIUL DSPI_0 LINFlexD_4 eMIOS_1	I/O O O I/O	M/S	Tristate	46	54	P2
PF[11]	PCR[91]	AF0 AF1 AF2 AF3 — —	GPIO[91] CS2_0 E1UC[3] — LIN4RX WKPU[15]	SIUL DSPI_0 eMIOS_1 — LINFlexD_4 WKPU	I/O O I/O — I I	S	Tristate	47	55	R1
PF[12]	PCR[92]	AF0 AF1 AF2 AF3	GPIO[92] E1UC[25] LIN5TX —	SIUL eMIOS_1 LINFlexD_5 —	I/O I/O O —	M/S	Tristate	43	51	P1
PF[13]	PCR[93]	AF0 AF1 AF2 AF3 — —	GPIO[93] E1UC[26] — — LIN5RX WKPU[16]	SIUL eMIOS_1 — — LINFlexD_5 WKPU	I/O I/O — — I I	S	Tristate	49	57	P3

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PG[10]	PCR[106]	AF0 AF1 AF2 AF3 —	GPIO[106] E0UC[24] E1UC[31] — SIN_4	SIUL eMIOS_0 eMIOS_1 — DSPI_4	I/O I/O I/O — I	S	Tristate	138	162	B13
PG[11]	PCR[107]	AF0 AF1 AF2 AF3	GPIO[107] E0UC[25] CS0_4 CS0_6	SIUL eMIOS_0 DSPI_4 DSPI_6	I/O I/O I/O I/O	M/S	Tristate	139	163	A16
PG[12]	PCR[108]	AF0 AF1 AF2 AF3 ALT4	GPIO[108] E0UC[26] SOUT_4 — TXD[2]	SIUL eMIOS_0 DSPI_4 — FEC	I/O I/O O — O	M/S	Tristate	116	140	F15
PG[13]	PCR[109]	AF0 AF1 AF2 AF3 ALT4	GPIO[109] E0UC[27] SCK_4 — TXD[3]	SIUL eMIOS_0 DSPI_4 — FEC	I/O I/O I/O — O	M/S	Tristate	115	139	F16
PG[14]	PCR[110]	AF0 AF1 AF2 AF3 —	GPIO[110] E1UC[0] LIN8TX — SIN_6	SIUL eMIOS_1 LINFlexD_8 — DSPI_6	I/O I/O O — I	S	Tristate	134	158	C13
PG[15]	PCR[111]	AF0 AF1 AF2 AF3 —	GPIO[111] E1UC[1] SOUT_6 — LIN8RX	SIUL eMIOS_1 DSPI_6 — LINFlexD_8	I/O I/O O — I	M/S	Tristate	135	159	D13
PH[0]	PCR[112]	AF0 AF1 AF2 AF3 ALT4 —	GPIO[112] E1UC[2] — — TXD[1] SIN_1	SIUL eMIOS_1 — — FEC DSPI_1	I/O I/O — — O I	M/S	Tristate	117	141	E15

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PI[0]	PCR[128]	AF0 AF1 AF2 AF3	GPIO[128] E0UC[28] LIN8TX —	SIUL eMIOS_0 LINFlexD_8 —	I/O I/O O —	S	Tristate	172	196	C5
PI[1]	PCR[129]	AF0 AF1 AF2 AF3 — —	GPIO[129] E0UC[29] — — WKPU[24] LIN8RX	SIUL eMIOS_0 — — WKPU LINFlexD_8	I/O I/O — — I I	S	Tristate	171	195	A4
PI[2]	PCR[130]	AF0 AF1 AF2 AF3	GPIO[130] E0UC[30] LIN9TX —	SIUL eMIOS_0 LINFlexD_9 —	I/O I/O O —	S	Tristate	170	194	D6
PI[3]	PCR[131]	AF0 AF1 AF2 AF3 — —	GPIO[131] E0UC[31] — — WKPU[23] LIN9RX	SIUL eMIOS_0 — — WKPU LINFlexD_9	I/O I/O — — I I	S	Tristate	169	193	B5
PI[4]	PCR[132]	AF0 AF1 AF2 AF3	GPIO[132] E1UC[28] SOUT_4 —	SIUL eMIOS_1 DSPI_4 —	I/O I/O O —	M/S	Tristate	143	167	A12
PI[5]	PCR[133]	AF0 AF1 AF2 AF3 ALT4	GPIO[133] E1UC[29] SCK_4 CS2_5 CS2_6	SIUL eMIOS_1 DSPI_4 DSPI_5 DSPI_6	I/O I/O I/O O O	M/S	Tristate	142	166	D12
PI[6]	PCR[134]	AF0 AF1 AF2 AF3 ALT4	GPIO[134] E1UC[30] CS0_4 CS0_5 CS0_6	SIUL eMIOS_1 DSPI_4 DSPI_5 DSPI_6	I/O I/O I/O I/O I/O	S	Tristate	11	11	D2

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PI[13]	PCR[141]	AF0 AF1 AF2 AF3 —	GPIO[141] CS1_3 CS1_2 — ADC0_S[21]	SIUL DSPI_3 DSPI_2 — ADC_0	I/O O O — I	S	Tristate	113	137	G14
PI[14]	PCR[142]	AF0 AF1 AF2 AF3 — —	GPIO[142] — — — ADC0_S[22] SIN_4	SIUL — — — ADC_0 DSPI_4	I/O — — — I I	S	Tristate	76	92	T12
PI[15]	PCR[143]	AF0 AF1 AF2 AF3 —	GPIO[143] CS0_4 CS2_2 — ADC0_S[23]	SIUL DSPI_4 DSPI_2 — ADC_0	I/O I/O O — I	S	Tristate	75	91	P11
PJ[0]	PCR[144]	AF0 AF1 AF2 AF3 —	GPIO[144] CS1_4 CS3_2 — ADC0_S[24]	SIUL DSPI_4 DSPI_2 — ADC_0	I/O O O — I	S	Tristate	74	90	R11
PJ[1]	PCR[145]	AF0 AF1 AF2 AF3 — —	GPIO[145] — — — ADC0_S[25] SIN_5	SIUL — — —— ADC_0 DSPI_5	I/O — — — I I	S	Tristate	73	89	N10
PJ[2]	PCR[146]	AF0 AF1 AF2 AF3 —	GPIO[146] CS0_5 CS0_6 CS0_7 ADC0_S[26]	SIUL DSPI_5 DSPI_6 DSPI_7 ADC_0	I/O I/O I/O I/O I	S	Tristate	72	88	R10

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PL[6]	PCR[182]	AF0 AF1 AF2 AF3	GPIO[182] — MDO4 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	K5
PL[7]	PCR[183]	AF0 AF1 AF2 AF3	GPIO[183] — MDO5 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	L5
PL[8]	PCR[184]	AF0 AF1 AF2 AF3 —	GPIO[184] — — — EVTI	SIUL — — — Nexus	I/O — — — I	S	Pull-up	—	—	M9
PL[9]	PCR[185]	AF0 AF1 AF2 AF3	GPIO[185] — MSEO —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	M10
PL[10]	PCR[186]	AF0 AF1 AF2 AF3	GPIO[186] — MCKO —	SIUL — Nexus —	I/O — O —	F/S	Tristate	—	—	M11
PL[11]	PCR[187]	AF0 AF1 AF2 AF3	GPIO[187] — — —	SIUL — — —	I/O — — —	M/S	Tristate	—	—	M12
PL[12]	PCR[188]	AF0 AF1 AF2 AF3	GPIO[188] — EVTO —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	F11
PL[13]	PCR[189]	AF0 AF1 AF2 AF3	GPIO[189] — MDO6 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	F10

Table 11. Recommended operating conditions (5.0 V) (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
$V_{DD\_HV\_ADC0}$ (5)	SR	Voltage on VDD_HV_ADC0 with respect to ground (V_{SS_HV})	—	4.5	5.5	V
			Voltage drop(2)	3.0	5.5	
			Relative to $V_{DD\_HV\_A}$(6)	$V_{DD\_HV\_A}$ – 0.1	$V_{DD\_HV\_A}$ + 0.1	
$V_{DD\_HV\_ADC1}$ (7)	SR	Voltage on VDD_HV_ADC1 with respect to ground (V_{SS_HV})	—	4.5	5.5	V
			Voltage drop(2)	3.0	5.5	
			Relative to $V_{DD\_HV\_A}$(6)	$V_{DD\_HV\_A}$ – 0.1	$V_{DD\_HV\_A}$ + 0.1	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS_HV})	—	V_{SS_HV} –0.1	—	V
			Relative to $V_{DD\_HV\_A/HV\_B}$	—	$V_{DD\_HV\_A/HV\_B}$ + 0.1	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
TV_{DD}	SR	$V_{DD\_HV\_A}$ slope to ensure correct power up(8)	—	—	0.5	V/µs
			—	0.5	—	V/min
T_{A} C-Grade Part	SR	Ambient temperature under bias	—	–40	85	°C
T_{J} C-Grade Part	SR	Junction temperature under bias	—	–40	110	
T_{A} V-Grade Part	SR	Ambient temperature under bias	—	–40	105	
T_{J} V-Grade Part	SR	Junction temperature under bias	—	–40	130	
T_{A} M-Grade Part	SR	Ambient temperature under bias	—	–40	125	
T_{J} M-Grade Part	SR	Junction temperature under bias	—	–40	150	

1. 100 nF EMI capacitance need to be provided between each VDD/VSS_HV pair.
2. Full device operation is guaranteed by design from 3.0 V–5.5 V. OSC functionality is guaranteed from the entire range 3.0V–5.5 V, the parametrics measured are at 3.0V and 5.5V (extreme voltage ranges to cover the range of operation). The parametrics might have some variation in the intermediate voltage range, but there is no impact to functionality.
3. 100 nF EMI capacitance needs to be provided between each VDD_LV/VSS_LV supply pair. 10 µF bulk capacitance needs to be provided as CREG on each VDD_LV pin.
4. This voltage is internally generated by the device and no external voltage should be supplied.
5. 100 nF capacitance needs to be provided between $V_{DD\_HV\_(ADC0/ADC1)}$/$V_{SS\_HV\_(ADC0/ADC1)}$ pair.
6. Both the relative and the fixed conditions must be met. For instance: If $V_{DD\_HV\_A}$ is 5.9 V, $V_{DD\_HV\_ADC0}$ maximum value is 6.0 V then, despite the relative condition, the max value is $V_{DD\_HV\_A}$ + 0.3 = 6.2 V.
7. PA3, PA7, PA10, PA11 and PE12 ADC_1 channels are coming from $V_{DD\_HV\_B}$ domain hence VDD_HV_ADC1 should be within ±100 mV of $V_{DD\_HV\_B}$ when these channels are used for ADC_1.

The internal voltage regulator requires external bulk capacitance (C_{REGn}) to be connected to the device to provide a stable low voltage digital supply to the device. Also required for stability is the C_{DEC2} capacitor at ballast collector. This is needed to minimize sharp injection current when ballast is turning ON. Apart from the bulk capacitance, user should connect EMI/decoupling cap (C_{REGP}) at each V_{DD_LV}/V_{SS_LV} pin pair.

3.8.1.1 Recommendations

- The external NPN driver must be BCP68 type.
- V_{DD_LV} should be implemented as a power plane from the emitter of the ballast transistor.
- 10 µF capacitors should be connected to the 4 pins closest to the outside of the package and should be evenly distributed around the package. For BGA packages, the balls should be used are D8, H14, R9, J3–one cap on each side of package.
  - There should be a track direct from the capacitor to this pin (pin also connects to V_{DD_LV} plane). The tracks ESR should be less than 100 mΩ.
  - The remaining V_{DD_LV} pins (exact number will vary with package) should be decoupled with 0.1 µF caps, connected to the pin as per 10 µF.

(see *Section 3.4: Recommended operating conditions*).

3.8.2 V_{DD_BV} options

- Option 1: V_{DD_BV} shared with $V_{DD\_HV\_A}$

  V_{DD_BV} must be star routed from $V_{DD\_HV\_A}$ from the common source. This is to eliminate ballast noise injection on the MCU.
- Option 2: V_{DD_BV} independent of the MCU supply

  V_{DD_BV} > 2.6 V for correct functionality. The device is not monitoring this supply hence the external component must meet the 2.6 V criteria through external monitoring if required.

Table 23. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
C_{REGn}	SR	—	External ballast stability capacitance	—	40	—	60	µF
R_{REG}	SR	—	Stability capacitor equivalent serial resistance	—	—	—	0.2	W
C_{REGP}	SR	—	Decoupling capacitance (Close to the pin)	$V_{DD\_HV\_A/HV\_B}/V_{SS\_HV}$ pair		100	—	nF
				V_{DD_LV}/V_{SS_LV} pair		100	—	nF
C_{DEC2}	SR	—	Stability capacitance regulator supply (Close to the ballast collector)	V_{DD_BV}/V_{SS_HV}	10	—	40	µF
V_{MREG}	CC	P	Main regulator output voltage	After trimming T_A = 25 °C	1.20	1.28	1.32	V

Table 23. Voltage regulator electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
I_{MREG}	SR	—	Main regulator current provided to V_{DD_LV} domain	—	—	—	350	mA
$I_{MREGINT}$	CC	D	Main regulator module current consumption	I_{MREG} = 200 mA	—	—	2	mA
				I_{MREG} = 0 mA	—	—	1	
V_{LPREG}	CC	P	Low power regulator output voltage	After trimming T_A = 25 °C	1.17	1.27	1.32	V
I_{LPREG}	SR	—	Low power regulator current provided to V_{DD_LV} domain	—	—	—	50	mA
$I_{LPREGINT}$	CC	D	Low power regulator module current consumption	I_{LPREG} = 15 mA; T_A = 55 °C	—	—	600	µA
		—		I_{LPREG} = 0 mA; T_A = 55 °C	—	20	—	
$I_{VREGREF}$	CC	D	Main LVDs and reference current consumption (low power and main regulator switched off)	T_A = 55 °C	—	2	—	µA
$I_{VREDLVD12}$	CC	D	Main LVD current consumption (switch-off during standby)	T_A = 55 °C	—	1	—	µA
$I_{DD\_HV\_A}$	CC	D	In-rush current on V_{DD_BV} during power-up	—	—	—	600 (3)	mA

1. $V_{DD\_HV\_A}$ = 3.3 V ± 10 % / 5.0 V ± 10 %, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. Inrush current is seen more like steps of 600 mA peak. The startup of the regulator happens in steps of 50 mV in ~25 steps to reach ~1.2 V V_{DD_LV}. Each step peak current is within 600 mA

3.8.3 Voltage monitor electrical characteristics

The device implements a Power-on Reset module to ensure correct power-up initialization, as well as four low voltage detectors to monitor the $V_{DD\_HV\_A}$ and the V_{DD_LV} voltage while device is supplied:

- POR monitors $V_{DD\_HV\_A}$ during the power-up phase to ensure device is maintained in a safe reset state
- LVDHV3 monitors $V_{DD\_HV\_A}$ to ensure device is reset below minimum functional supply
- LVDHV5 monitors $V_{DD\_HV\_A}$ when application uses device in the 5.0 V±10 % range
- LVDLVCOR monitors power domain No. 1 (PD1)
- LVDLVBKP monitors power domain No. 0 (PD0). VDD_LV is same as PD0 supply.

Note: When enabled, PD2 (RAM retention) is monitored through LVD_DIGBKP.

9. Subject to change, Configuration: 1 × e200z4d + 4 kbit/s Cache, 1 × e200z0h (1/2 system frequency), CSE, 1 × eDMA (10 ch.), 6 × FlexCAN (4 × 500 kbit/s, 2 × 125 kbit/s), 4 × LINFlexD (20 kbit/s), 6 × DSPI (2 × 2 Mbit/s, 3 × 4 Mbit/s, 1 × 10 Mbit/s), 16 × Timed I/O, 16 × ADC Input, 1 × FlexRay (2 ch., 10 Mbit/s), 1 × FEC (100 Mbit/s), 1 × RTC, 4 PIT channels, 1 × SWT, 1 × STM. For lower pin count packages reduce the amount of timed I/O's and ADC channels. RUN current measured with typical application with accesses on both code flash and RAM.
10. This value is obtained from limited sample set.
11. Data Flash Power Down. Code Flash in Low Power. SIRC 128 kHz and FIRC 16 MHz ON. 16 MHz XTAL clock. FlexCAN: instances: 0, 1, 2 ON (clocked but no reception or transmission), instances: 4, 5, 6 clocks gated. LINFlex: instances: 0, 1, 2 ON (clocked but no reception or transmission), instance: 3-9 clocks gated. eMIOS: instance: 0 ON (16 channels on PA[0]-PA[11] and PC[12]-PC[15]) with PWM 20 kHz, instance: 1 clock gated. DSPI: instance: 0 (clocked but no communication, instance: 1-7 clocks gated). RTC/API ON. PIT ON. STM ON. ADC ON but no conversion except 2 analog watchdogs.
12. Only for the "P" classification: No clock, FIRC 16 MHz OFF, SIRC128 kHz ON, PLL OFF, HPvreg OFF, LPVreg ON. All possible peripherals off and clock gated. Flash in power down mode.
13. Only for the "P" classification: LPreg ON, HPVreg OFF, 96 KB RAM ON, device configured for minimum consumption, all possible modules switched-off. Measurement condition assumes T_j = Ta.
14. LPreg ON, HPVreg OFF, 64 KB RAM ON, device configured for minimum consumption, all possible modules switched-off. Measurement condition assumes T_j = Ta.
15. LPreg ON, HPVreg OFF, 8 KB RAM ON, device configured for minimum consumption, all possible modules switched OFF. Measurement condition assumes T_j = Ta.

3.10 Flash memory electrical characteristics

3.10.1 Program/Erase characteristics

Table 26 shows the code flash memory program and erase characteristics.

Table 26. Code flash memory—Program and erase specifications

Symbol		C	Parameter	Value				Unit
				Min	Typ(1)	Initial max(2)	Max(3)	
$T_{dwprogram}$	CC	C	Double word (64 bits) program time(4)	—	18	50	500	µs
$T_{16Kpperase}$			16 KB block pre-program and erase time	—	200	500	5000	ms
$T_{32Kpperase}$			32 KB block pre-program and erase time	—	300	600	5000	ms
$T_{128Kpperase}$			128 KB block pre-program and erase time	—	600	1300	5000	ms
T_{eslat}		D	Erase Suspend Latency	—	—	30	30	µs
t_{ESRT}(5)		C	Erase Suspend Request Rate	20	—	—	—	ms
t_{PABT}		D	Program Abort Latency	—	—	10	10	µs
t_{EAPT}		D	Erase Abort Latency	—	—	30	30	µs

1. Typical program and erase times assume nominal supply values and operation at 25 °C. All times are subject to change pending device characterization.
2. Initial factory condition: < 100 program/erase cycles, 25 °C, typical supply voltage.
3. The maximum program and erase times occur after the specified number of program/erase cycles. These maximum values are characterized but not guaranteed.
4. Actual hardware programming times. This does not include software overhead.
5. It is Time between erase suspend resume and the next erase suspend request.

Table 27 shows the data flash memory program and erase characteristics.

3.11.2 Electromagnetic interference (EMI)

The product is monitored in terms of emission based on a typical application. This emission test conforms to the IEC61967-1 standard, which specifies the general conditions for EMI measurements.

Table 32. EMI radiated emission measurement(1)(2)

Symbol		C	Parameter	Conditions		Value			Unit
						Min	Typ	Max	
—	SR	—	Scan range	—		0.150		1000	MHz
f_{CPU}	SR	—	Operating frequency	—		—	120	—	MHz
V_{DD_LV}	SR	—	LV operating voltages	—		—	1.28	—	V
S_{EMI}	CC	T	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP176 package Test conforming to IEC 61967-2, f_{OSC} = 40 MHz/f_{CPU} = 120 MHz	No PLL frequency modulation	—	—	18	dBµV
					± 2% PLL frequency modulation	—	—	14(3)	dBµV

1. EMI testing and I/O port waveforms per IEC 61967-1, -2, -4.
2. For information on conducted emission and susceptibility measurement (norm IEC 61967-4), please contact your local marketing representative.
3. All values need to be confirmed during device validation.

3.11.3 Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity.

3.11.3.1 Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pin). This test conforms to the AEC-Q100-002/-003/-011 standard. For more details, refer to the application note *Electrostatic Discharge Sensitivity Measurement* (AN1181).

Table 33. ESD absolute maximum ratings(1)(2)

Symbol	Ratings	Conditions	Class	Max value(3)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	T_A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)	T_A = 25 °C conforming to AEC-Q100-003	M2	200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charged Device Model)	T_A = 25 °C conforming to AEC-Q100-011	C3A	500	
				750 (corners)	

Table 36. Fast external crystal oscillator (4 to 40 MHz) electrical characteristics (continued)

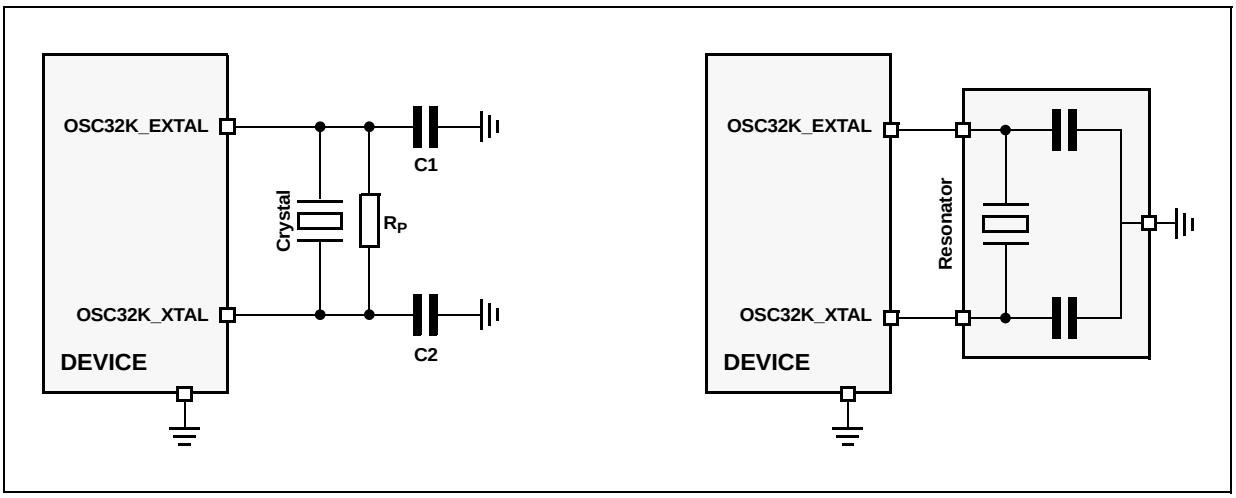
Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input high level CMOS (Schmitt Trigger)	Oscillator bypass mode	$0.65V_{DD\_HV\_A}$	—	$V_{DD\_HV\_A}$ + 0.4	V
V_{IL}	SR	P	Input low level CMOS (Schmitt Trigger)	Oscillator bypass mode	–0.3	—	$0.35V_{DD\_HV\_A}$	V

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. Based on ATE Cz
4. Stated values take into account only analog module consumption but not the digital contributor (clock tree and enabled peripherals).

3.13 Slow external crystal oscillator (32 kHz) electrical characteristics

The device provides a low power oscillator/resonator driver.

Figure 12. Crystal oscillator and resonator connection scheme



Note: OSC32K_XTAL/OSC32K_EXTAL must not be directly used to drive external circuits.

Figure 14. Slow external crystal oscillator (32 kHz) electrical characteristics

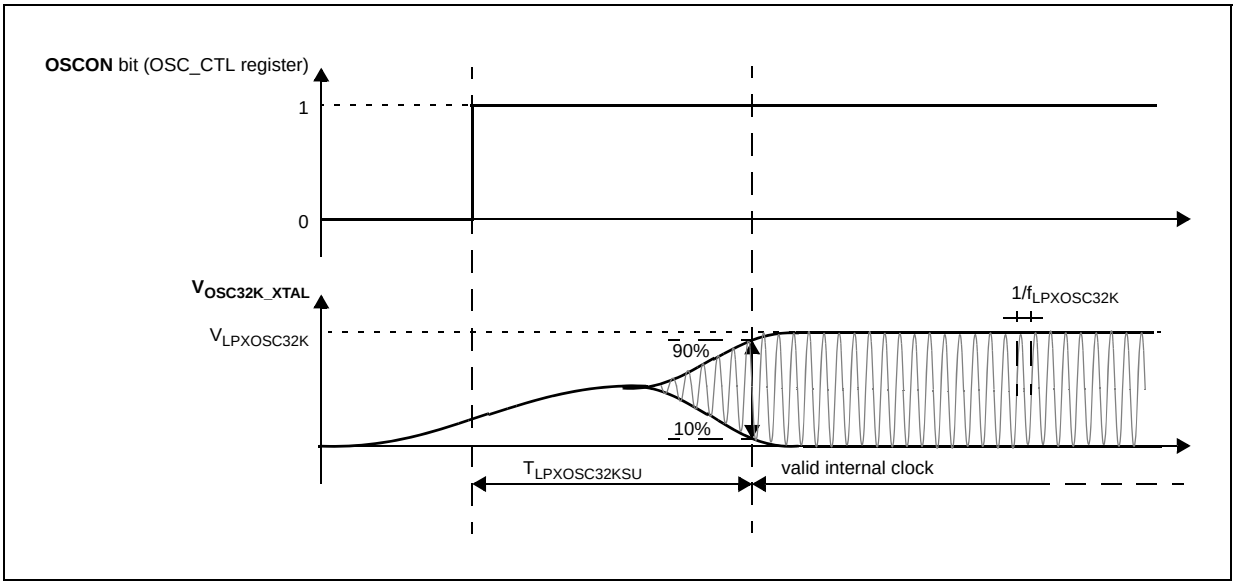


Table 38. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
f_{SXOSC}	SR	—	Slow external crystal oscillator frequency	—	32	32.768	40	kHz
g_{mSXOSC}	CC	—	Slow external crystal oscillator transconductance	V_{DD} = 3.3 V ± 10%,	13[3]	—	33[3]	µA/V
				V_{DD} = 5.0 V ± 10%	15[3]	—	35[3]	
V_{SXOSC}	CC	T	Oscillation amplitude	—	1.2	1.4	1.7	V
$I_{SXOSCBIAS}$	CC	T	Oscillation bias current	—	1.2	—	4.4	µA
I_{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	—	7	µA
$T_{SXOSCSU}$	CC	T	Slow external crystal oscillator start-up time	—	—	—	2[4]	s

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. Based on ATE CZ
4. Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

3.14 FMPLL electrical characteristics

The device provides a frequency-modulated phase-locked loop (FMPLL) module to generate a fast system clock from the main oscillator driver.

Table 39. FMPLL electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
f_{PLLIN}	SR	—	FMPLL reference clock[3]	—	4	—	64	MHz
Δ_{PLLIN}	SR	—	FMPLL reference clock duty cycle[3]	—	40	—	60	%
f_{PLLOUT}	CC	P	FMPLL output clock frequency	—	16	—	120	MHz
f_{CPU}	SR	—	System clock frequency	—	—	—	120 + 2%[4]	MHz
f_{FREE}	CC	P	Free-running frequency	—	20	—	150	MHz
t_{LOCK}	CC	P	FMPLL lock time	Stable oscillator (f_{PLLIN} = 16 MHz)		40	100	µs
Δt_{LTJIT}	CC	—	FMPLL long term jitter	f_{PLLIN} = 40 MHz (resonator), f_{PLLCLK} @ 120 MHz, 4000 cycles	—	—	6 (for < 1ppm)	ns
I_{PLL}	CC	C	FMPLL consumption	T_A = 25 °C	—	—	3	mA

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. PLLIN clock retrieved directly from 4-40 MHz XOSC or 16 MIRC. Input characteristics are granted when oscillator is used in functional mode. When bypass mode is used, oscillator input clock should verify f_{PLLIN} and Δ_{PLLIN}.
4. f_{CPU} 120 + 2% MHz can be achieved at 125 °C.

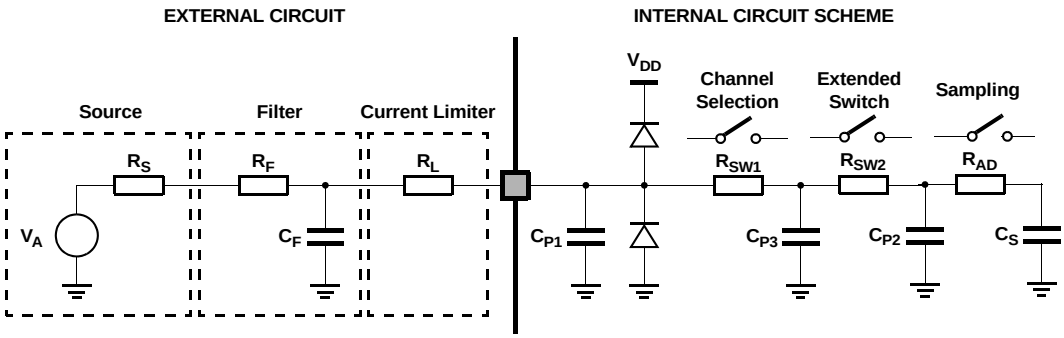
3.15 Fast internal RC oscillator (16 MHz) electrical characteristics

The device provides a 16 MHz main internal RC oscillator. This is used as the default clock at the power-up of the device and can also be used as input to PLL.

Table 40. Fast internal RC oscillator (16 MHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
f_{FIRC}	CC	P	Fast internal RC oscillator high frequency	T_A = 25 °C, trimmed	—	16	—	MHz
	SR	—		—	12		20	

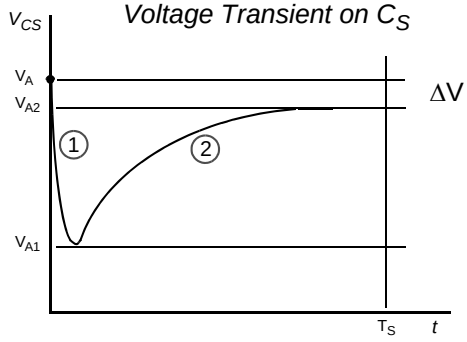
Figure 17. Input equivalent circuit (extended channels)



R_S Source Impedance
R_F Filter Resistance
C_F Filter Capacitance
R_L Current Limiter Resistance
R_{SW} Channel Selection Switch Impedance (two contributions R_{SW1} and R_{SW2})
R_{AD}Sampling Switch Impedance
C_P Pin Capacitance (three contributions, C_{P1}, C_{P2} and C_{P3})
C_S Sampling Capacitance

A second aspect involving the capacitance network shall be considered. Assuming the three capacitances C_F, C_{P1} and C_{P2} initially charged at the source voltage V_A (refer to the equivalent circuit reported in *Figure 16*): when the sampling phase is started (A/D switch close), a charge sharing phenomena is installed.

Figure 18. Transient behavior during sampling phase



$\Delta V < 0.5$ LSB

$\tau_1 < (R_{SW} + R_{AD})\, C_S << T_S$

$\tau_2 = R_L\,(C_S + C_{P1} + C_{P2})$

In particular two different transient periods can be distinguished:

- A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Equation 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

Figure 34. Nexus output timing

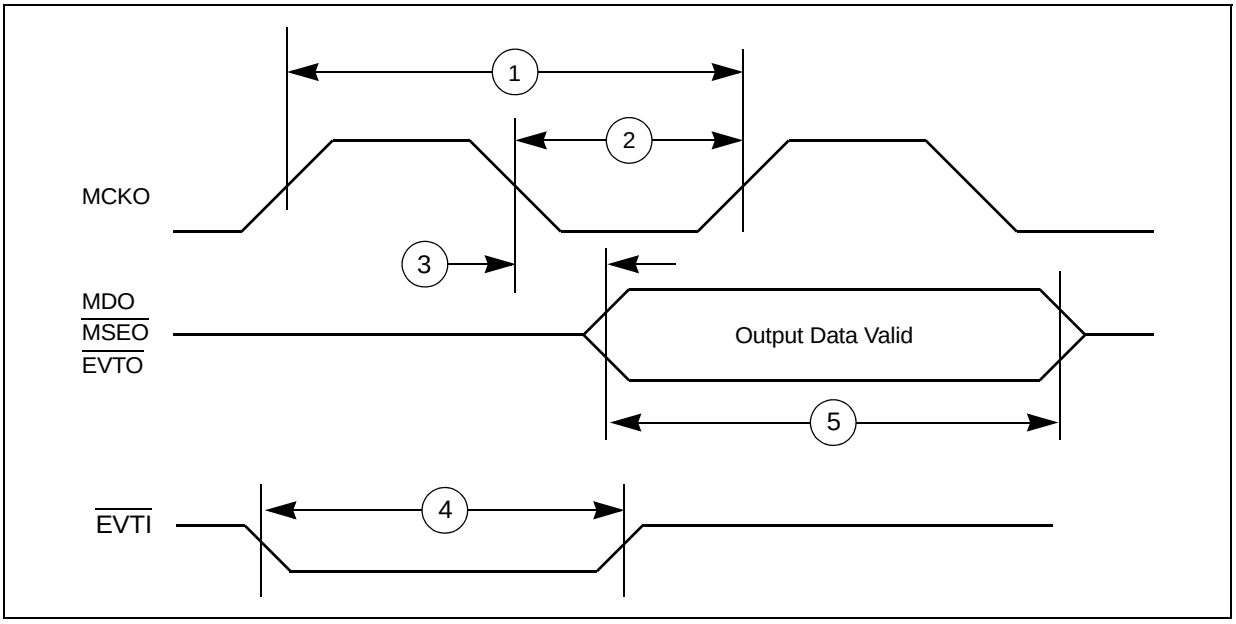


Table 57. Revision history (continued)

Date	Revision	Changes
04-Mar-2013	5 (cont.)	– Updated the min, max and typical values of $V_{LVDLVCORL}$ and $V_{LVDLVBKPL}$ in *Table 24: Low voltage monitor electrical characteristics* – Updated values of gmFXOSC in *Table 36: Fast external crystal oscillator (4 to 40 MHz) electrical characteristics* – Updated values of gmSXOSC in *Table 38: Slow external crystal oscillator (32 kHz) electrical characteristics* – Updated the footnote 5 for T_{ADC0_C} in *Table 43: ADC conversion characteristics (10-bit ADC_0)* – Updated the footnotes of *Table 25: Low voltage power domain electrical characteristics*
17-Sep-2013	6	– Updated Disclaimer
28-Nov-2014	7	– Removed occurrences of 208BGA from *Table 2: SPC564Bxx and SPC56ECxx family comparison*. – Added PM[3] and PM[4] in the figure note 1 of *Figure 4: 256-pin BGA configuration*. – Added a table note in*Table 20: I/O supplies*. – Updated *Figure 8: Voltage regulator capacitance connection* and added a note in this figure. – Removed before trimming value for V_{MREG}, updated after trimming min value of V_{MREG} from 1.24 V to 1.20 V, updated after trimming min value of V_{LPREG} from 1.225 V to 1.17 V, updated after trimming typical value of V_{LPREG} from 1.25 V to 1.27 V and updated after trimming max value of V_{LPREG} from 1.275 V to 1.32 V in *Table 23: Voltage regulator electrical characteristics*. – Changed min value of $V_{LVDLVCORL}$ and $V_{LVDLVBKPL}$ from 1.12 V to 1.08 V, and removed typical value of $V_{LVDLVCORL}$ and $V_{LVDLVBKPL}$ in *Table 24: Low voltage monitor electrical characteristics* – Updated max values at 120 MHz for I_{DDRUN} from 200 mA to 208 mA and from 270 mA to 280 mA; updated max value at T_A = 125 °C for I_{DDHALT} from 80 mA to 100 mA; updated max value at T_A = 25 °C for I_{DDSTOP} from 1.2 mA to 5 mA and at T_A = 125 °C from 60 mA to 72 mA; updated max value at T_A = 25 °C for $I_{DDSTDBY3}$ from 75 µA to 96 µA and at T_A = 125 °C from 1200 µA to 2400 µA; updated max value at T_A = 25 °C for $I_{DDSTDBY2}$ from 70 µA to 92 µA and at T_A = 125 °C from 1100 µA to 2000 µA; updated max value at T_A = 25 °C for $I_{DDSTDBY1}$ from 65 µA to 85 µA and at T_A = 125 °C from 650 µA to 1100 µA; updated 1st footnote in *Table 25: Low voltage power domain electrical characteristics*. – Added a footnote below *Table 29: Flash memory read access timing*. – Updated the formula in Eq. 11 in *Section 3.17.1.1: Input impedance and ADC accuracy*. – Updated legend in *Figure 16: Input equivalent circuit (precise channels)* – Updated min and max values for g_{mFXOSC} at V_{DD} = 5.0 V ± 10% from 4 mA/V to 6.5 mA/V and from 20 mA/V to 25 mA/V in *Table 36: Fast external crystal oscillator (4 to 40 MHz) electrical characteristics* – Added *Figure 17: Input equivalent circuit (extended channels)*. – Updated t_{ADC0_PU} value to 1.5 as max and added footnote for I_{INJ} in *Table 43: ADC conversion characteristics (10-bit ADC_0)*.

Table 57. Revision history (continued)

Date	Revision	Changes
28-Nov-2014	7 (cont.)	– Added Category column in *Table 44: Conversion characteristics (12-bit ADC_1)*. – Added the IDD_HV_ADC0 values in *Table 49: On-chip peripherals current consumption*.
16-Jun-2015	8	Updated *Figure 37: LQFP176 package mechanical drawing* and *Figure 40: Ordering information scheme*.
11-Mar-2016	9	– Added package silhouette on the cover page – Removed *Figure 4: LBGA208 configuration* – Removed LBGA208 column in *Table 4: System pin descriptions* and in *Table 5: Functional port pin descriptions* – *Table 12: LQFP thermal characteristics*: for "$R_{\theta JA}$" row, changed Max value relating to conditions "Single-layer board—1s" and "Four-layer board—2s2p" from "TBD" to "43" and "33.9", respectively – Removed *Table 13: LBGA208 thermal characteristics* – *Table 13: LBGA256 thermal characteristics*: for "$R_{\theta JA}$" row, changed Max value relating to conditions "Single-layer board—1s" and "Four-layer board—2s2p" from "TBD" to "44.3" and "31", respectively – Removed LBGA208 row in *Table 20: I/O supplies* – Removed *Section 4.2.3: LBGA208 package mechanical drawing* – In *Table 25: Low voltage power domain electrical characteristics*, updated notes "Only for the "P" classification: LPreg ON, HPVreg OFF, 96 KB RAM ON, device configured for...", "LPreg ON, HPVreg OFF, 64 KB RAM ON, device configured for...", and "LPreg ON, HPVreg OFF, 8 KB RAM ON, device configured for..." – In *Table 49: On-chip peripherals current consumption*, changed IDD_HV_ADC1 value from "300 × f_{periph}" to "300"